

Transistors

2.5V Drive Nch MOS FET

RJK005N03

●Structure

Silicon N-channel MOS FET

●Features

- 1) Low On-resistance.
- 2) Low voltage drive (2.5V drive).

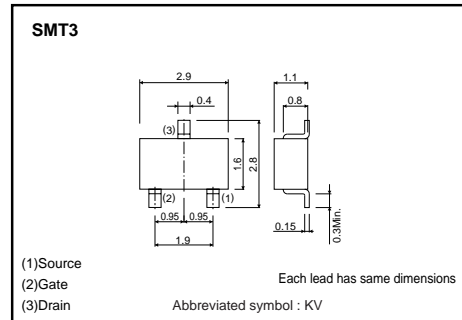
●Applications

Switching

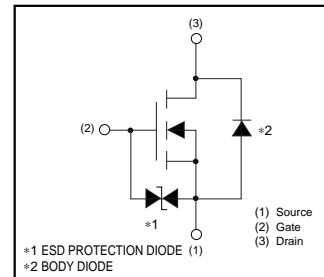
●Packaging specifications and h_{FE}

Type	Package	Taping
	Code	T146
	Basic ordering unit (pieces)	3000
RJK005N03		○

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	30	V
Gate-source voltage	V _{GSS}	±12	V
Drain current	Continuous	I _D	±500 mA
	Pulsed	I _{DP} *1	±2.0 A
Source current (Body Diode)	Continuous	I _S	200 mA
	Pulsed	I _{SP} *1	800 mA
Total power dissipation	P _D *2	200	mW
Channel temperature	T _{ch}	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

*1 Pw≤10μs, Duty cycles≤1%

*2 Each terminal mounted on a recommended land

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	R _{th(ch-a)} *	625	°C/W

* Each terminal mounted on a recommended land

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	±10	μA	V _{GS} =±12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	30	–	–	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	1	μA	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.8	–	1.5	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	R _{DS (on)} *	–	400	580	mΩ	I _D = 500mA, V _{GS} = 4.5V
		–	420	600	mΩ	I _D = 500mA, V _{GS} = 4V
		–	650	940	mΩ	I _D = 500mA, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs} *	0.5	–	–	S	V _{DS} = 10V, I _D = 500mA
Input capacitance	C _{iss}	–	60	–	pF	V _{DS} = 10V
Output capacitance	C _{oss}	–	24	–	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	–	12	–	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	–	9	–	ns	V _{DD} ≐ 15V I _D = 250mA
Rise time	t _r *	–	11	–	ns	V _{GS} = 4V
Turn-off delay time	t _{d (off)} *	–	16	–	ns	R _L =60Ω
Fall time	t _f *	–	31	–	ns	R _G =10Ω
Total gate charge	Q _g *	–	2.0	4.0	nC	V _{DD} ≐ 24V
Gate-source charge	Q _{gs} *	–	0.6	–	nC	V _{GS} = 4V
Gate-drain charge	Q _{gd} *	–	0.7	–	nC	I _D = 500mA

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	–	–	1.2	V	I _S = 500mA, V _{GS} =0V

*Pulsed

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